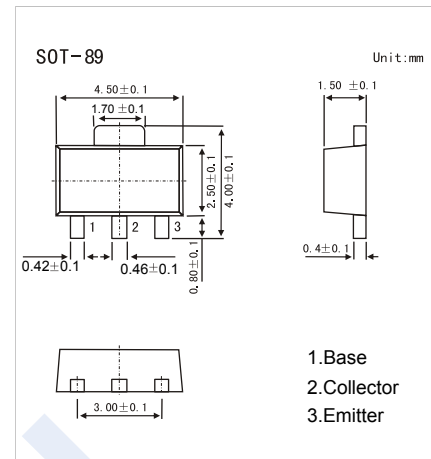


NPN Transistors

2SC3439

■ Features

- High h_{FE} : $h_{FE}=400$ to 1800
- High collector current
- Low collector to emitter saturation voltage
- High collector dissipation $P_c=500\text{mW}$
- Small package for mounting
- Complementary to 2SA1369

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	30	V
Collector - Emitter Voltage	V_{CEO}	25	
Emitter - Base Voltage	V_{EB0}	6	
Collector Current - Continuous	I_C	1.5	A
Peak Collector Current	I_{CM}	3	
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = 100\mu\text{A}$, $I_E = 0$	30			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 1\text{mA}$, $R_{BE} = \infty$	25			
Emitter-base breakdown voltage	V_{EB0}	$I_E = 100\mu\text{A}$, $I_C = 0$	6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 20\text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}$, $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1\text{A}$, $I_B = 20\text{mA}$		0.2	0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1\text{A}$, $I_B = 20\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6\text{V}$, $I_C = 500\text{mA}$	400		1800	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		17		pF
Transition frequency	f_T	$V_{CE} = 10\text{V}$, $I_C = 10\text{mA}$		130		MHz

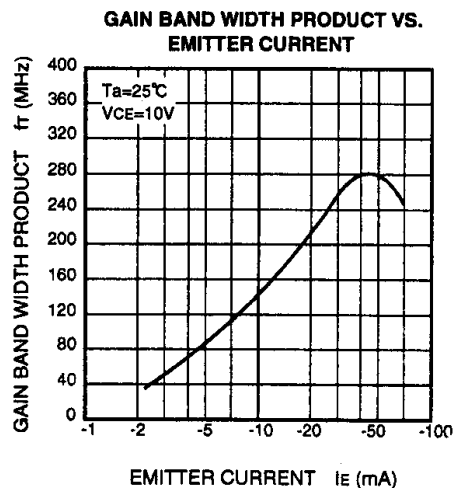
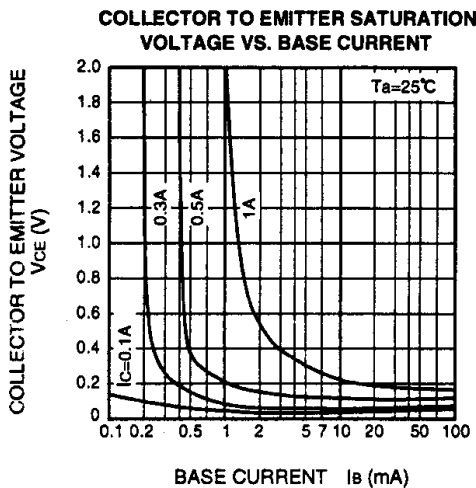
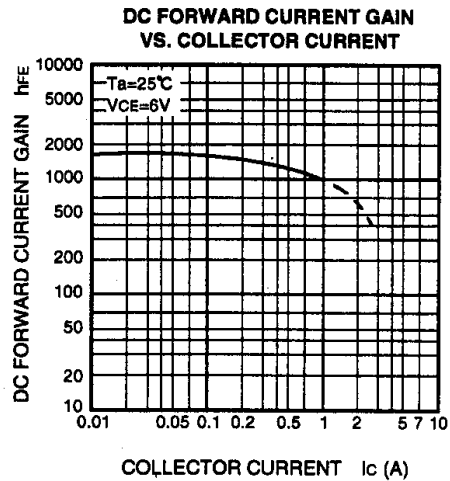
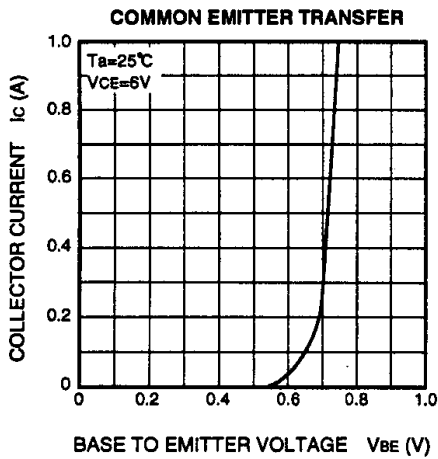
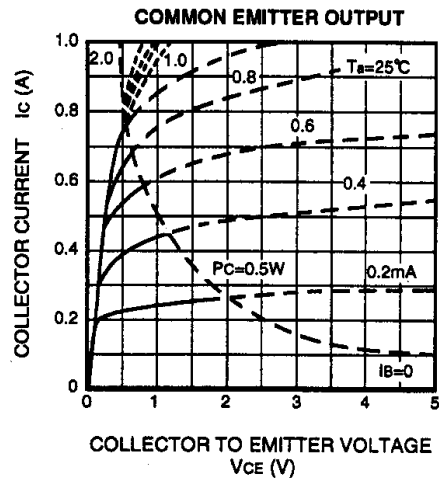
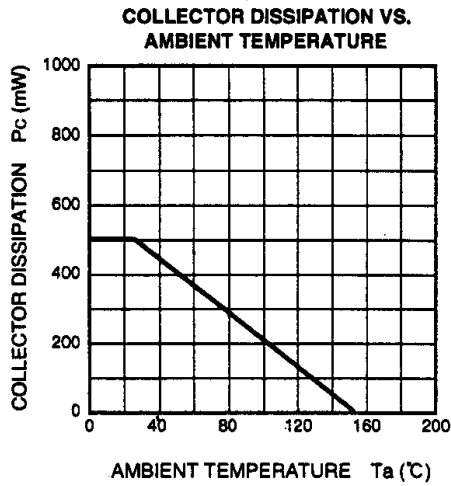
■ Classification of h_{FE}

Marking	HG	HH	HJ
Range	400-800	600-1200	900-1800

NPN Transistors

2SC3439

■ Typical Characteristics



NPN Transistors

2SC3439

■ Typical Characteristics

